

Features

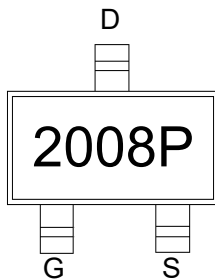
- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-15V	18m Ω @-4.5V	-8A
	25m Ω @-2.5V	

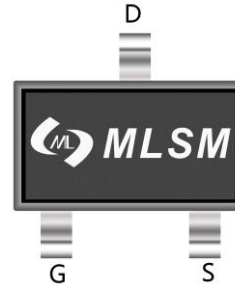
Application

- Battery protection
- Load switch
- Power management

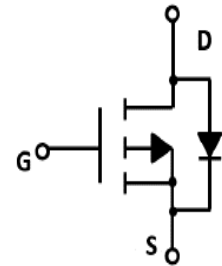


2008P: Device code

Marking and pin assignment



SOT-23-3L top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	-15	V
V_{GS}	Gate-Source Voltage	± 12	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ -8	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ -32	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ -8	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 1.2	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	105	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSK2008P	SOT-23-3L	2008P	3,000	45,000	180,000	7" reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-15	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-15V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-5A	--	18	25	mΩ
		V _{GS} =-2.5V, I _D =-2A	--	25	35	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-9V, V _{GS} =0V, f=1MHz	--	1010	--	pF
C _{OSS}	Output Capacitance		--	135	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	109	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-9V, I _D =-5.6A, V _{GS} =-4.5V	--	11	--	nC
Q _{gs}	Gate Source Charge		--	2.2	--	nC
Q _{gd}	Gate Drain Charge		--	2.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-9V, I _D =-1A, V _{GS} =-4.5V, R _G =2.5Ω	--	8	--	nS
t _r	Turn-on Rise Time		--	36	--	nS
t _{d(off)}	Turn-Off Delay Time		--	77	--	nS
t _f	Turn-Off Fall Time		--	56	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	TJ=25℃, Is=-8A	--	--	-1.2	V

Typical Operating Characteristics

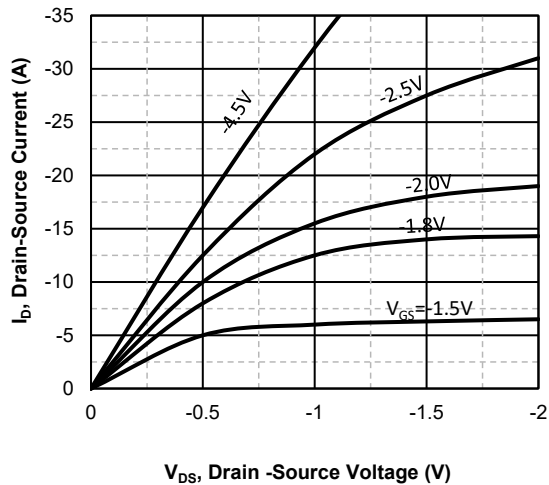


Fig1. Typical Output Characteristics

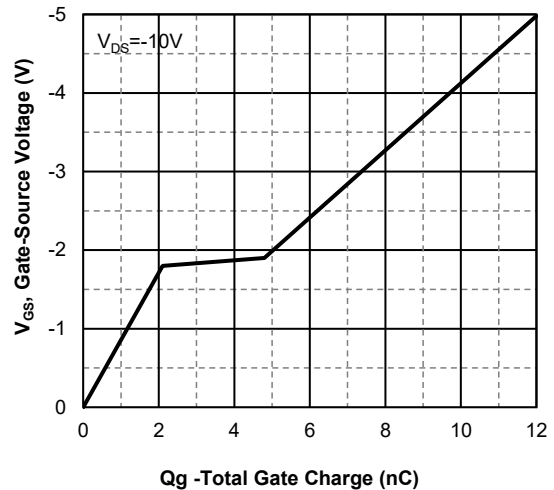


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

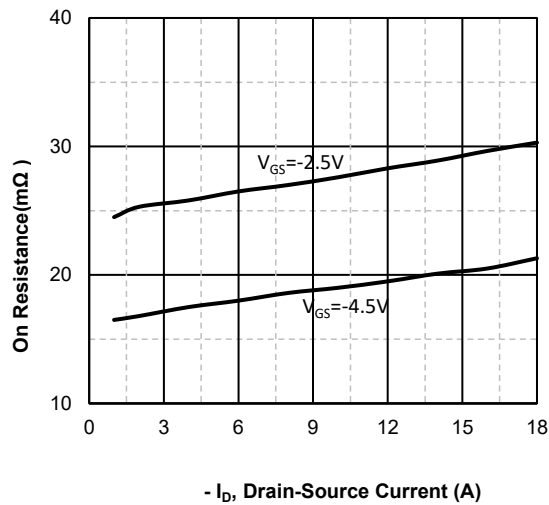


Fig3. Drain-Source on Resistance

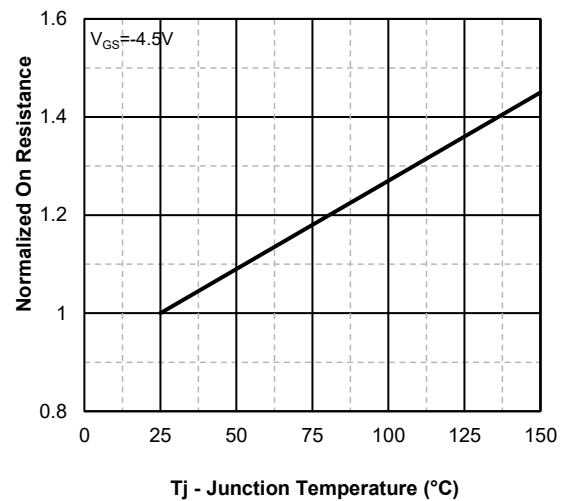


Fig4. Normalized On-Resistance Vs. Temperature

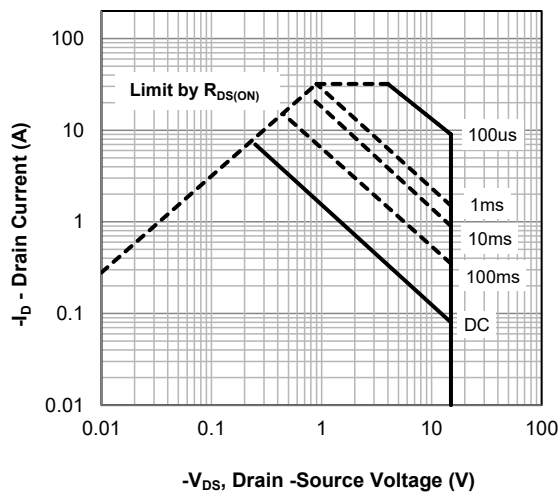


Fig5. Maximum Safe Operating Area

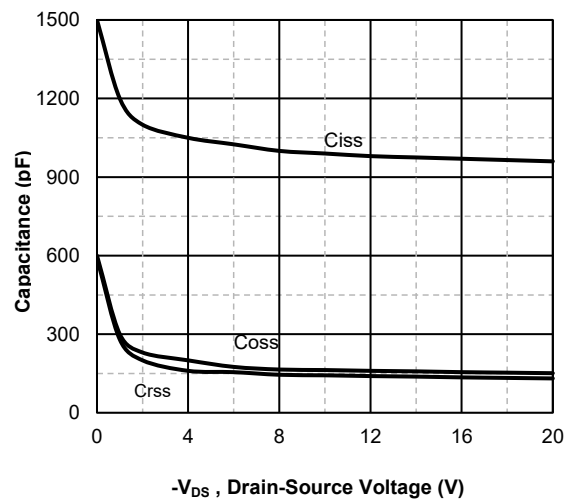
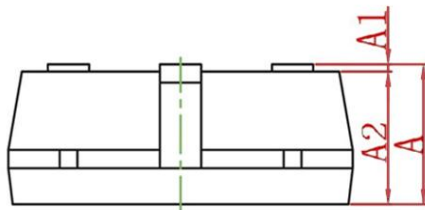
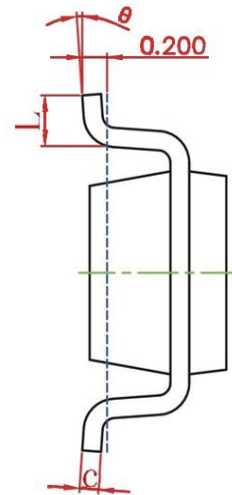
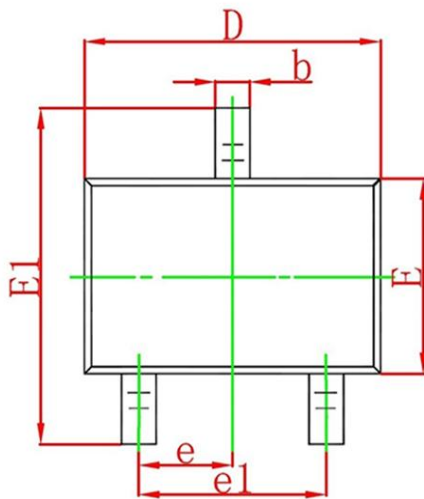


Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°